

THE UNITED STATES PATENT AND TRADEMARK OFFICE

Docket No: Q77954

Fumio MATSUMOTO

lication of

Appln. No.: 10/575,081

Group Art Unit: 1722

Confirmation No.: 8636 Examiner: Not Yet Assigned

Filed: November 28, 2006

SEMICONDUCTOR For: COMPOUND SINGLE CRYSTAL AND **PRODUCTION**

PROCESS THEREOF

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §§ 1.97 and 1.98

MAIL STOP AMENDMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, Applicant hereby notifies the U.S. Patent and Trademark Office of the documents which are listed on the attached PTO/SB/08 A & B (modified) form and/or listed herein and which the Examiner may deem material to patentability of the claims of the above-identified application.

One copy of each of the listed documents is submitted herewith, except for the following: U.S. patents and/or U.S. patent publications; and co-pending non-provisional U.S. applications filed after June 30, 2003.

The present Information Disclosure Statement is being filed: (1) No later than three months from the application's filing date; (2) Before the mailing date of the first Office Action on the merits (whichever is later); or (3) Before the mailing date of the first Office Action after filing a request for continued examination (RCE) under §1.114, and therefore, no Statement under 37 C.F.R. § 1.97(e) or fee under 37 C.F.R. § 1.17(p) is required.

INFORMATION DISCLOSURE STATEMEN'T

U.S. Appln. No.: 10/575,081

Attorney Docket No.: Q77954

In compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant encloses herewith a copy of a Communication from a foreign patent office in a counterpart application citing such documents (German Office Action for German Patent Application No. 11 2004 001 866.8 dated July 10, 2007), together with an English-language version (if not already included) of at least that portion of the Communication indicating the degree of relevance found by the foreign patent office.

Additionally, in compliance with the concise explanation requirement under 37 C.F.R. § 1.98(a)(3) for foreign language documents, Applicant states that U.S. Patent Application Publication No. US 2007/0079751 A1 corresponds to DE 11 2004 001 269.

JP 3-40987 was previously submitted in the Information Disclosure Statement filed April 7, 2006.

The submission of the listed documents is not intended as an admission that any such document constitutes prior art against the claims of the present application. Applicant does not waive any right to take any action that would be appropriate to antedate or otherwise remove any listed document as a competent reference against the claims of the present application.

The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account.

Respectfully submitted,

Abraham J. Rosner

Registration No. 33,276

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WASHINGTON OFFICE 23373

CUSTOMER NUMBER

Date: August 20, 2007

PATENT APPLICATION



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Docket No: Q77954

Fumio MATSUMOTO

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PROCESS THEREOF

STATEMENT UNDER 37 C.F.R. § 1.97(e)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The undersigned hereby states, upon information and belief:

That each item of information contained in the Information Disclosure Statement filed concurrently herewith was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of said Information Disclosure Statement.

Respectfully submitted,

SUGHRUE MION, PLLC

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washington office 23373
customer number

Date: August 20, 2007

Abraham J. Rosner

Registration No. 33,276

		Complete if Known		
Substitute for Form 1449 A & B/PTO			Application Number	10/575,081
INFO	DMATION	DISCLOSURE	Confirmation Number	8636
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U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document Number		Publication Date		
		Number	Kind Code ² (if known)	MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
		US 2007/0079751	Al	04-12-2007	MATSUMOTO	
		US				
		US				
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FOREIGN PATENT DOCUMENTS							
Examiner Cite No.1	Foreign Patent Document			Publication Date	Name of Patentee or		
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)	MM-DD-YYYY	Applicant of Cited Document	Translation ⁶
		DE	11 2004 001 269	Т5	07-20-2006	SHOWA DENKO KK	Abstract (of corresponding US 2007/0079751 A1)
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NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶	
		Yasumasa OKADA, et al.; "Mechanism of a Reduction of Dislocation Densities in Vertical-Gradient-Freeze-Grown GaAs Single Crystals"; Japanese Journal of Applied Physics; Vol. 29; No. 11; November 1990; pp. L 1954-L 1956	·.·	
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Examiner Signature	Date Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or follow the hyperlink from the title of the document to the intranet. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.